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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	512
Total RAM Bits	-
Number of I/O	81
Number of Gates	12000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	100-LQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex256-tqg100i

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1 – eX FPGA Architecture and Characteristics

General Description

The eX family of FPGAs is a low-cost solution for low-power, high-performance designs. The inherent low power attributes of the antifuse technology, coupled with an additional low static power mode, make these devices ideal for power-sensitive applications. Fabricated with an advanced 0.22 μm CMOS antifuse technology, these devices achieve high performance with no power penalty.

eX Family Architecture

Microsemi eX family is implemented on a high-voltage twin-well CMOS process using 0.22 μm design rules. The eX family architecture uses a “sea-of-modules” structure where the entire floor of the device is covered with a grid of logic modules with virtually no chip area lost to interconnect elements or routing. Interconnection among these logic modules is achieved using Microsemi patented metal-to-metal programmable antifuse interconnect elements. The antifuse interconnect is made up of a combination of amorphous silicon and dielectric material with barrier metals and has an “on” state resistance of 25Ω with a capacitance of 1.0fF for low-signal impedance. The antifuses are normally open circuit and, when programmed, form a permanent low-impedance connection. The eX family provides two types of logic modules, the register cell (R-cell) and the combinatorial cell (C-cell).

The R-cell contains a flip-flop featuring asynchronous clear, asynchronous preset, and clock enable (using the S0 and S1 lines) control signals ([Figure 1-1](#)). The R-cell registers feature programmable clock polarity selectable on a register-by-register basis. This provides additional flexibility while allowing mapping of synthesized functions into the eX FPGA. The clock source for the R-cell can be chosen from either the hard-wired clock or the routed clock.

The C-cell implements a range of combinatorial functions up to five inputs ([Figure 1-2 on page 1-2](#)). Inclusion of the DB input and its associated inverter function enables the implementation of more than 4,000 combinatorial functions in the eX architecture in a single module.

Two C-cells can be combined together to create a flip-flop to imitate an R-cell via the use of the CC macro. This is particularly useful when implementing non-timing-critical paths and when the design engineer is running out of R-cells. More information about the CC macro can be found in the [Maximizing Logic Utilization in eX, SX and SX-A FPGA Devices Using CC Macros](#) application note.

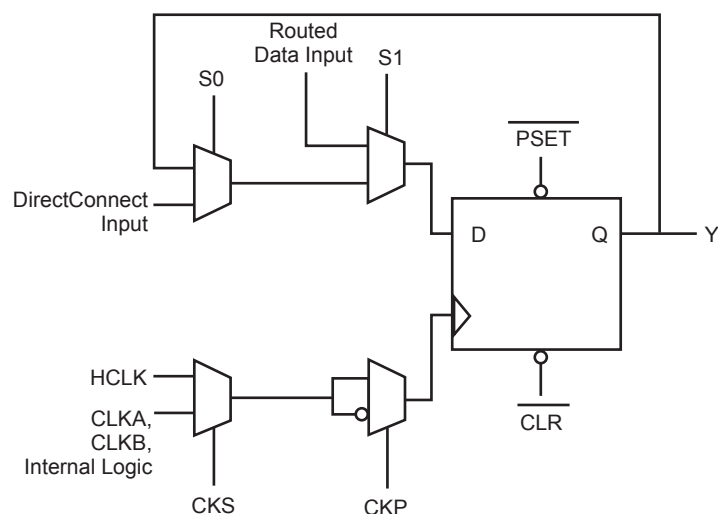


Figure 1-1 • R-Cell

Module Organization

C-cell and R-cell logic modules are arranged into horizontal banks called Clusters, each of which contains two C-cells and one R-cell in a C-R-C configuration.

Clusters are further organized into modules called SuperClusters for improved design efficiency and device performance, as shown in Figure 1-3. Each SuperCluster is a two-wide grouping of Clusters.

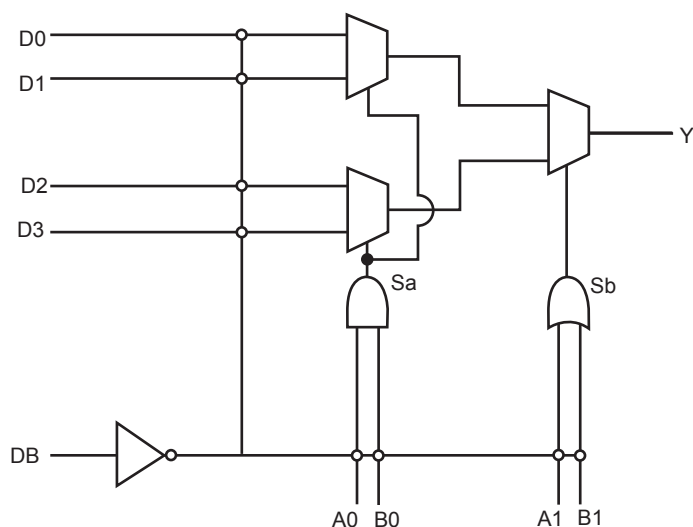


Figure 1-2 • C-Cell

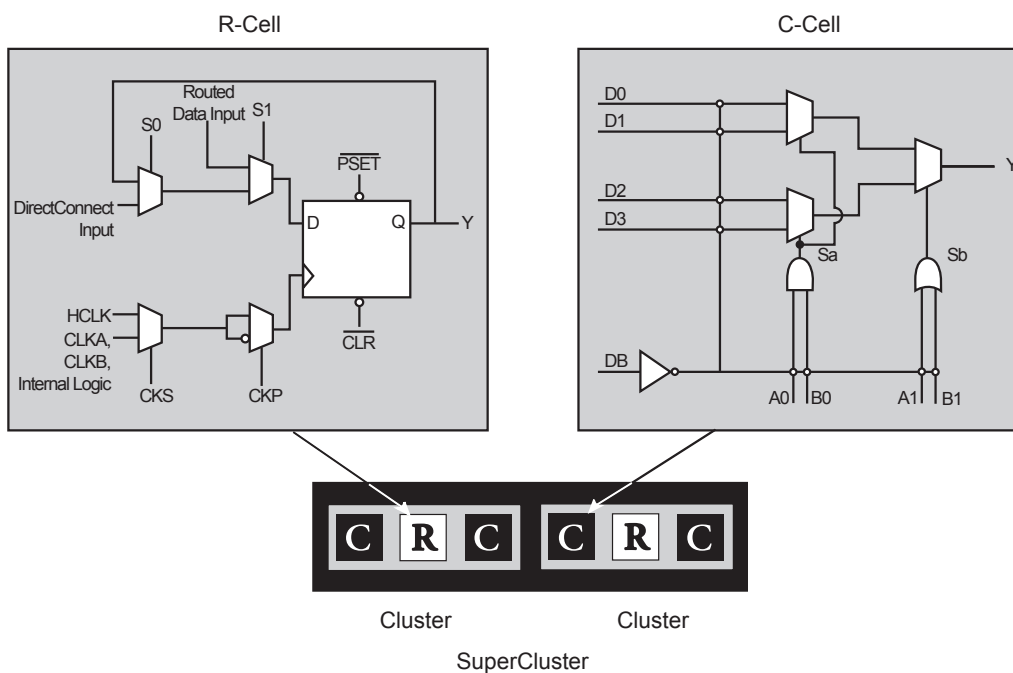


Figure 1-3 • Cluster Organization

Other Architectural Features

Performance

The combination of architectural features described above enables eX devices to operate with internal clock frequencies exceeding 350 MHz for very fast execution of complex logic functions. The eX family is an optimal platform upon which the functionality previously contained in CPLDs can be integrated. eX devices meet the performance goals of gate arrays, and at the same time, present significant improvements in cost and time to market. Using timing-driven place-and-route tools, designers can achieve highly deterministic device performance.

User Security

Microsemi FuseLock advantage provides the highest level of protection in the FPGA industry against unauthorized modifications. In addition to the inherent strengths of the architecture, special security fuses that are intended to prevent internal probing and overwriting are hidden throughout the fabric of the device. They are located such that they cannot be accessed or bypassed without destroying the rest of the device, making Microsemi antifuse FPGAs highly resistant to both invasive and more subtle noninvasive attacks.

Look for this symbol to ensure your valuable IP is secure. The FuseLock Symbol on the FPGA ensures that the device is safeguarded to cryptographic attacks.



Figure 1-7 • FuseLock

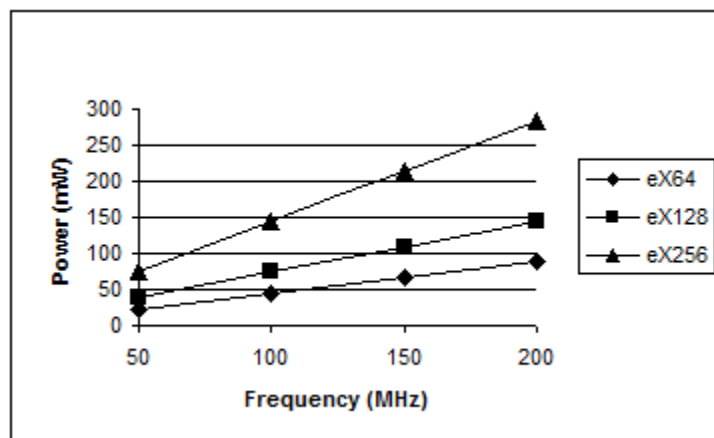
For more information, refer to [Implementation of Security in Microsemi Antifuse FPGAs](#) application note.

I/O Modules

Each I/O on an eX device can be configured as an input, an output, a tristate output, or a bidirectional pin. Even without the inclusion of dedicated I/O registers, these I/Os, in combination with array registers, can achieve clock-to-out (pad-to-pad) timing as fast as 3.9 ns. I/O cells in eX devices do not contain embedded latches or flip-flops and can be inferred directly from HDL code. The device can easily interface with any other device in the system, which in turn enables parallel design of system components and reduces overall design time.

All unused I/Os are configured as tristate outputs by Microsemi's Designer software, for maximum flexibility when designing new boards or migrating existing designs. Each I/O module has an available pull-up or pull-down resistor of approximately 50 k Ω that can configure the I/O in a known state during power-up. Just shortly before V_{CCA} reaches 2.5 V, the resistors are disabled and the I/Os will be controlled by user logic.

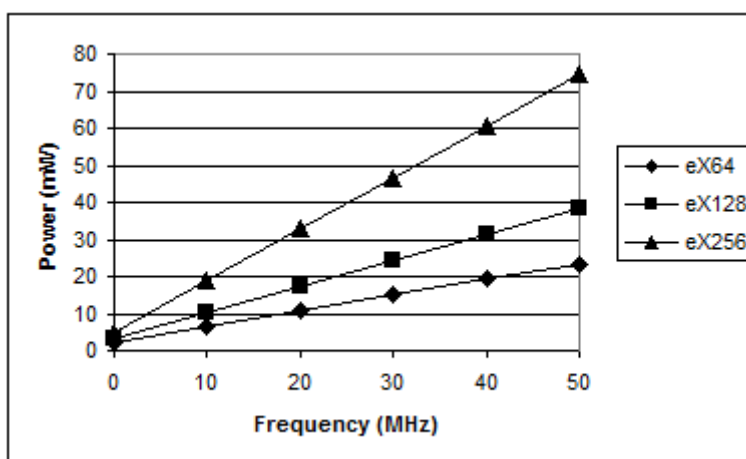
Figure 1-8 to Figure 1-11 on page 1-9 show some sample power characteristics of eX devices.



Notes:

1. Device filled with 16-bit counters.
2. VCCA, VCCI = 2.7 V, device tested at room temperature.

Figure 1-8 • eX Dynamic Power Consumption – High Frequency



Notes:

1. Device filled with 16-bit counters.
2. VCCA, VCCI = 2.7 V, device tested at room temperature.

Figure 1-9 • eX Dynamic Power Consumption – Low Frequency

Boundary Scan Testing (BST)

All eX devices are IEEE 1149.1 compliant. eX devices offer superior diagnostic and testing capabilities by providing Boundary Scan Testing (BST) and probing capabilities. These functions are controlled through the special test pins (TMS, TDI, TCK, TDO and TRST). The functionality of each pin is defined by two available modes: Dedicated and Flexible, and is described in [Table 1-4](#). In the dedicated test mode, TCK, TDI, and TDO are dedicated pins and cannot be used as regular I/Os. In flexible mode (default mode), TMS should be set HIGH through a pull-up resistor of 10 k Ω . TMS can be pulled LOW to initiate the test sequence.

Table 1-4 • Boundary Scan Pin Functionality

Dedicated Test Mode	Flexible Mode
TCK, TDI, TDO are dedicated BST pins	TCK, TDI, TDO are flexible and may be used as I/Os
No need for pull-up resistor for TMS and TDI	Use a pull-up resistor of 10 k Ω on TMS

Dedicated Test Mode

In Dedicated mode, all JTAG pins are reserved for BST; designers cannot use them as regular I/Os. An internal pull-up resistor is automatically enabled on both TMS and TDI pins, and the TMS pin will function as defined in the IEEE 1149.1 (JTAG) specification.

To select Dedicated mode, users need to reserve the JTAG pins in Microsemi's Designer software by checking the **Reserve JTAG** box in the Device Selection Wizard ([Figure 1-12](#)). JTAG pins comply with LVTTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O. Refer to the ["3.3 V LVTTTL Electrical Specifications"](#) section and ["5.0 V TTL Electrical Specifications"](#) section on [page 1-18](#) for detailed specifications.



Figure 1-12 • Device Selection Wizard

Flexible Mode

In Flexible Mode, TDI, TCK and TDO may be used as either user I/Os or as JTAG input pins. The internal resistors on the TMS and TDI pins are disabled in flexible JTAG mode, and an external 10 k Ω pull-resistor to V_{CC1} is required on the TMS pin.

To select the Flexible mode, users need to clear the check box for **Reserve JTAG** in the Device Selection Wizard in Microsemi's Designer software. The functionality of TDI, TCK, and TDO pins is controlled by the BST TAP controller. The TAP controller receives two control inputs, TMS and TCK. Upon power-up, the TAP controller enters the Test-Logic-Reset state. In this state, TDI, TCK, and TDO function as user I/Os. The TDI, TCK, and TDO pins are transformed from user I/Os into BST pins when the TMS pin is LOW at the first rising edge of TCK. The TDI, TCK, and TDO pins return to user I/Os when TMS is held HIGH for at least five TCK cycles.

Designer software is a place-and-route tool and provides a comprehensive suite of backend support tools for FPGA development. The Designer software includes timing-driven place-and-route, and a world-class integrated static timing analyzer and constraints editor. With the Designer software, a user can lock his/her design pins before layout while minimally impacting the results of place-and-route. Additionally, the back-annotation flow is compatible with all the major simulators and the simulation results can be cross-probed with Silicon Explorer II, Microsemi integrated verification and logic analysis tool. Another tool included in the Designer software is the SmartGen core generator, which easily creates popular and commonly used logic functions for implementation into your schematic or HDL design. Microsemi's Designer software is compatible with the most popular FPGA design entry and verification tools from companies such as Mentor Graphics, Synplicity, Synopsys, and Cadence Design Systems. The Designer software is available for both the Windows and UNIX operating systems.

Related Documents

Datasheet

eX Automotive Family FPGAs

www.microsemi.com/soc/documents/eX_Auto_DS.pdf

Application Notes

Maximizing Logic Utilization in eX, SX and SX-A FPGA Devices Using CC Macros

www.microsemi.com/soc/documents/CC_Macro_AN.pdf

Implementation of Security in Microsemi Antifuse FPGAs

www.microsemi.com/soc/documents/Antifuse_Security_AN.pdf

Microsemi eX, SX-A, and RT54SX-S I/Os

www.microsemi.com/soc/documents/antifuseIO_AN.pdf

Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications

www.microsemi.com/soc/documents/HotSwapColdSparing_AN.pdf

Design For Low Power in Microsemi Antifuse FPGAs

www.microsemi.com/soc/documents/Low_Power_AN.pdf

Programming Antifuse Devices

www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf

User Guides

Silicon Sculptor II User's Guide

www.microsemi.com/soc/documents/SiliSculptII_Sculpt3_ug.pdf

Miscellaneous

Libero IDE flow

www.microsemi.com/soc/products/tools/libero/flow.html

2.5 V / 3.3 V /5.0 V Operating Conditions

Table 1-9 • Absolute Maximum Ratings*

Symbol	Parameter	Limits	Units
V _{CCI}	DC Supply Voltage for I/Os	–0.3 to +6.0	V
V _{CCA}	DC Supply Voltage for Array	–0.3 to +3.0	V
V _I	Input Voltage	–0.5 to +5.75	V
V _O	Output Voltage	–0.5 to +V _{CCI}	V
T _{STG}	Storage Temperature	–65 to +150	°C

Note: *Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the Recommended Operating Conditions.

Table 1-10 • Recommended Operating Conditions

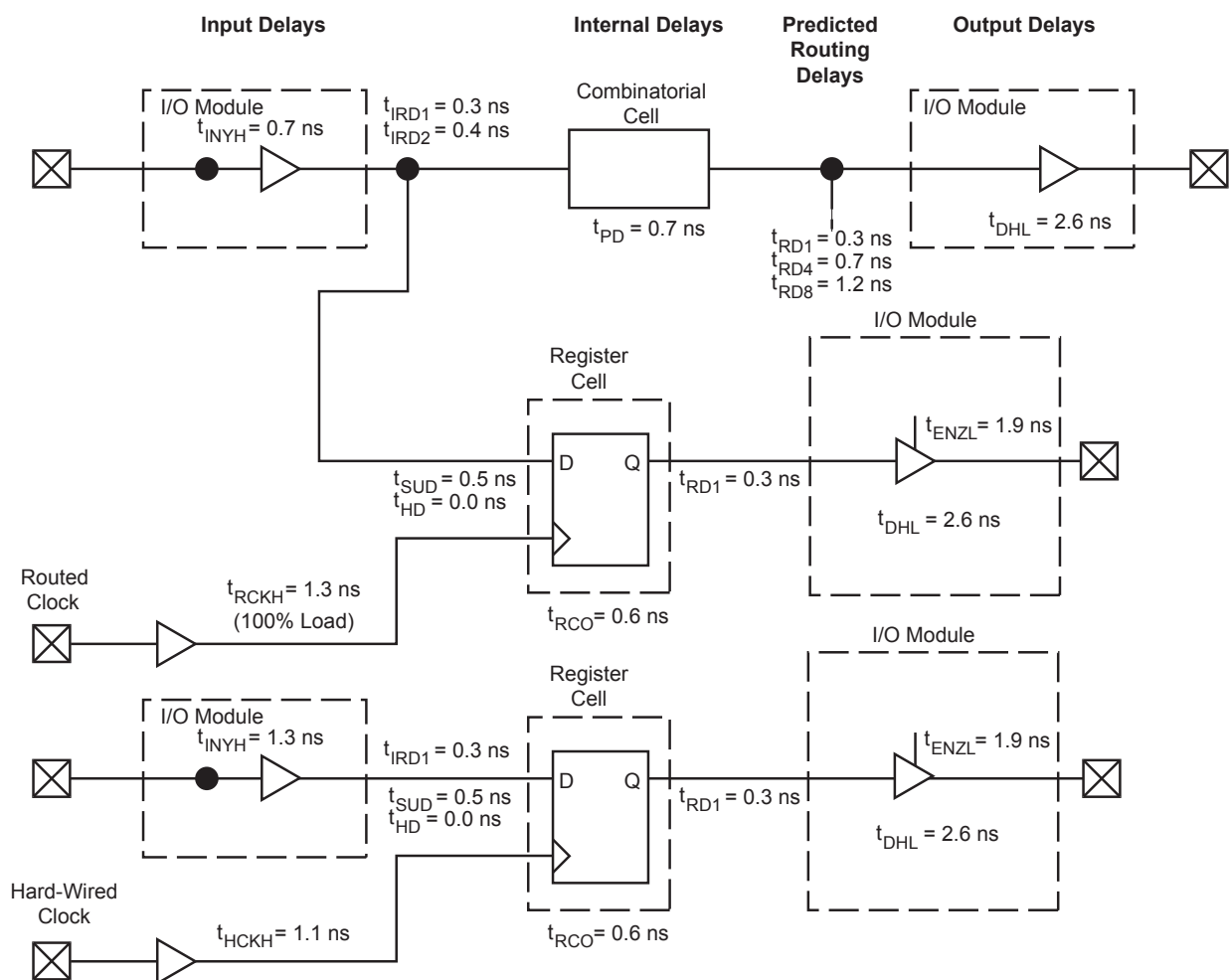
Parameter	Commercial	Industrial	Units
Temperature Range*	0 to +70	–40 to +85	°C
2.5V Power Supply Range (V _{CCA} , V _{CCI})	2.3 to 2.7	2.3 to 2.7	V
3.3V Power Supply Range (V _{CCI})	3.0 to 3.6	3.0 to 3.6	V
5.0V Power Supply Range (V _{CCI})	4.75 to 5.25	4.75 to 5.25	V

Note: *Ambient temperature (T_A).

Table 1-11 • Typical eX Standby Current at 25°C

Product	V _{CCA} = 2.5 V V _{CCI} = 2.5 V	V _{CCA} = 2.5 V V _{CCI} = 3.3 V	V _{CCA} = 2.5 V V _{CCI} = 5.0 V
eX64	397 µA	497 µA	700 µA
eX128	696 µA	795 µA	1,000 µA
eX256	698 µA	796 µA	2,000 µA

eX Timing Model



Note: Values shown for eX128-P, worst-case commercial conditions (5.0 V, 35 pF Pad Load).

Figure 1-14 • eX Timing Model

Hardwired Clock

$$\text{External Setup} = t_{INYH} + t_{IRD1} + t_{SUD} - t_{HCKH}$$

$$= 0.7 + 0.3 + 0.5 - 1.1 = 0.4 \text{ ns}$$

Clock-to-Out (Pad-to-Pad), typical

$$= t_{HCKH} + t_{RCO} + t_{RD1} + t_{DHL}$$

$$= 1.1 + 0.6 + 0.3 + 2.6 = 4.6 \text{ ns}$$

Routed Clock

$$\text{External Setup} = t_{INYH} + t_{IRD2} + t_{SUD} - t_{RCKH}$$

$$= 0.7 + 0.4 + 0.5 - 1.3 = 0.3 \text{ ns}$$

Clock-to-Out (Pad-to-Pad), typical

$$= t_{RCKH} + t_{RCO} + t_{RD1} + t_{DHL}$$

$$= 1.3 + 0.6 + 0.3 + 2.6 = 4.8 \text{ ns}$$

Input Buffer Delays

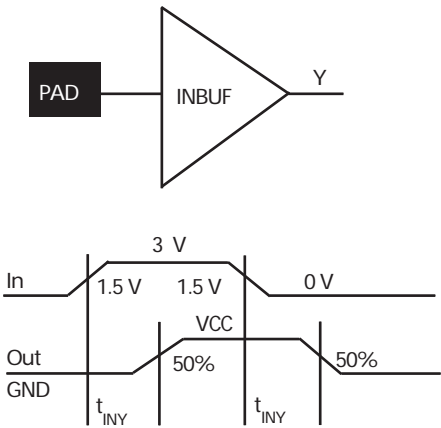


Table 1-14 • Input Buffer Delays

C-Cell Delays

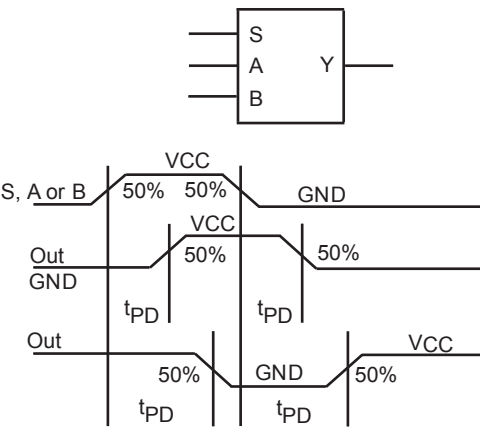


Table 1-15 • C-Cell Delays

Cell Timing Characteristics

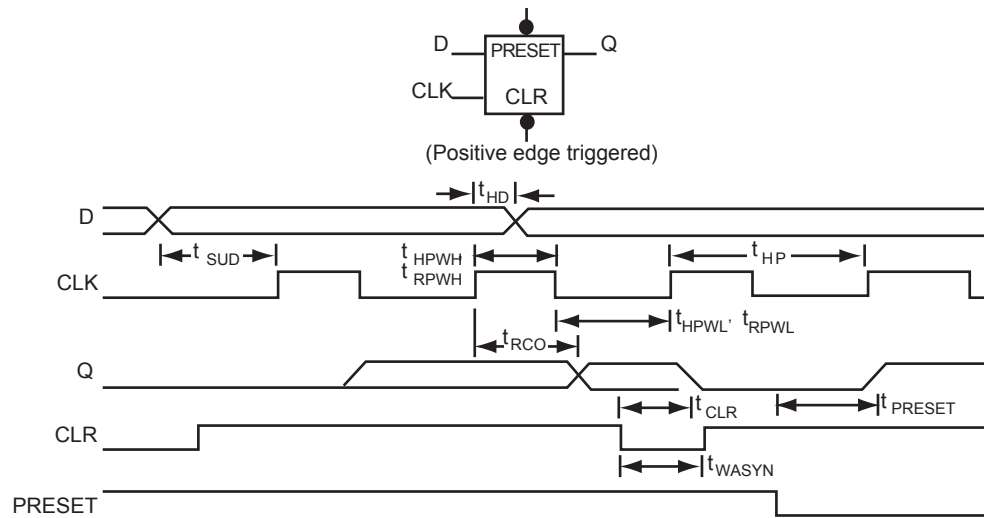


Figure 1-16 • Flip-Flops

Timing Characteristics

Timing characteristics for eX devices fall into three categories: family-dependent, device-dependent, and design-dependent. The input and output buffer characteristics are common to all eX family members. Internal routing delays are device-dependent. Design dependency means actual delays are not determined until after placement and routing of the user's design are complete. Delay values may then be determined by using the Timer utility or performing simulation with post-layout delays.

Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment prior to placement and routing. Up to six percent of the nets in a design may be designated as critical.

Long Tracks

Some nets in the design use long tracks. Long tracks are special routing resources that span multiple rows, columns, or modules. Long tracks employ three to five antifuse connections. This increases capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, no more than six percent of nets in a fully utilized device require long tracks. Long tracks contribute approximately 4 ns to 8.4 ns delay. This additional delay is represented statistically in higher fanout routing delays.

Timing Derating

eX devices are manufactured with a CMOS process. Therefore, device performance varies according to temperature, voltage, and process changes. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature, and best-case processing. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature, and worst-case processing.

Temperature and Voltage Derating Factors

Table 1-16 • Temperature and Voltage Derating Factors
(Normalized to Worst-Case Commercial, $T_J = 70^\circ\text{C}$, $V_{CCA} = 2.3\text{V}$)

VCCA	Junction Temperature (T_J)						
	–55	–40	0	25	70	85	125
2.3	0.79	0.80	0.87	0.88	1.00	1.04	1.13
2.5	0.74	0.74	0.81	0.83	0.93	0.97	1.06
2.7	0.69	0.70	0.76	0.78	0.88	0.91	1.00

Table 1-18 • eX Family Timing Characteristics
(Worst-Case Commercial Conditions VCCA = 2.3 V, VCCI = 4.75 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
Dedicated (Hard-Wired) Array Clock Networks								
t _{HCKH}	Input LOW to HIGH (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t _{HCKL}	Input HIGH to LOW (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t _{HPWH}	Minimum Pulse Width HIGH	1.4		2.0		2.8		ns
t _{HPWL}	Minimum Pulse Width LOW	1.4		2.0		2.8		ns
t _{HCKSW}	Maximum Skew		<0.1		<0.1		<0.1	ns
t _{HP}	Minimum Period	2.8		4.0		5.6		ns
f _{HMAX}	Maximum Frequency		357		250		178	MHz
Routed Array Clock Networks								
t _{RCKH}	Input LOW to HIGH (Light Load) (Pad to R-Cell Input) MAX.		1.1		1.6		2.2	ns
t _{RCKL}	Input HIGH to LOW (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t _{RCKH}	Input LOW to HIGH (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t _{RCKL}	Input HIGH to LOW (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t _{RCKH}	Input LOW to HIGH (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t _{RCKL}	Input HIGH to LOW (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t _{RPWH}	Min. Pulse Width HIGH	1.5		2.1		3.0		ns
t _{RPWL}	Min. Pulse Width LOW	1.5		2.1		3.0		ns
t _{RCKSW} *	Maximum Skew (Light Load)		0.2		0.3		0.4	ns
t _{RCKSW} *	Maximum Skew (50% Load)		0.1		0.2		0.3	ns
t _{RCKSW} *	Maximum Skew (100% Load)		0.1		0.1		0.2	ns

Note: *Clock skew improves as the clock network becomes more heavily loaded.

Table 1-20 • eX Family Timing Characteristics
(Worst-Case Commercial Conditions VCCA = 2.3 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
2.5 V LVCMOS Output Module Timing¹ (VCCI = 2.3 V)								
t _{DLH}	Data-to-Pad LOW to HIGH		3.3		4.7		6.6	ns
t _{DHL}	Data-to-Pad HIGH to LOW		3.5		5.0		7.0	ns
t _{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		11.6		16.6		23.2	ns
t _{ENZL}	Enable-to-Pad, Z to L		2.5		3.6		5.1	ns
t _{ENZLS}	Enable-to-Pad Z to L—Low Slew		11.8		16.9		23.7	ns
t _{ENZH}	Enable-to-Pad, Z to H		3.4		4.9		6.9	ns
t _{ENLZ}	Enable-to-Pad, L to Z		2.1		3.0		4.2	ns
t _{ENHZ}	Enable-to-Pad, H to Z		2.4		5.67		7.94	ns
d _{TLH}	Delta Delay vs. Load LOW to HIGH		0.034		0.046		0.066	ns/pF
d _{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d _{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
3.3 V LVTTTL Output Module Timing¹ (VCCI = 3.0 V)								
t _{DLH}	Data-to-Pad LOW to HIGH		2.8		4.0		5.6	ns
t _{DHL}	Data-to-Pad HIGH to LOW		2.7		3.9		5.4	ns
t _{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		9.7		13.9		19.5	ns
t _{ENZL}	Enable-to-Pad, Z to L		2.2		3.2		4.4	ns
t _{ENZLS}	Enable-to-Pad Z to L—Low Slew		9.7		13.9		19.6	ns
t _{ENZH}	Enable-to-Pad, Z to H		2.8		4.0		5.6	ns
t _{ENLZ}	Enable-to-Pad, L to Z		2.8		4.0		5.6	ns
t _{ENHZ}	Enable-to-Pad, H to Z		2.6		3.8		5.3	ns
d _{TLH}	Delta Delay vs. Load LOW to HIGH		0.02		0.03		0.046	ns/pF
d _{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d _{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
5.0 V TTL Output Module Timing* (VCCI = 4.75 V)								
t _{DLH}	Data-to-Pad LOW to HIGH		2.0		2.9		4.0	ns
t _{DHL}	Data-to-Pad HIGH to LOW		2.6		3.7		5.2	ns
t _{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		6.8		9.7		13.6	ns
t _{ENZL}	Enable-to-Pad, Z to L		1.9		2.7		3.8	ns
t _{ENZLS}	Enable-to-Pad Z to L—Low Slew		6.8		9.8		13.7	ns
t _{ENZH}	Enable-to-Pad, Z to H		2.1		3.0		4.1	ns
t _{ENLZ}	Enable-to-Pad, L to Z		3.3		4.8		6.6	ns

Note: *Delays based on 35 pF loading.

Pin Description

CLKA/B Routed Clock A and B

These pins are clock inputs for clock distribution networks. Input levels are compatible with standard TTL or LVTTTL specifications. The clock input is buffered prior to clocking the R-cells. If not used, this pin must be set LOW or HIGH on the board. It must not be left floating.

GND Ground

LOW supply voltage.

HCLK Dedicated (Hardwired) Array Clock

This pin is the clock input for sequential modules. Input levels are compatible with standard TTL or LVTTTL specifications. This input is directly wired to each R-cell and offers clock speeds independent of the number of R-cells being driven. If not used, this pin must be set LOW or HIGH on the board. It must not be left floating.

I/O Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Based on certain configurations, input and output levels are compatible with standard TTL or LVTTTL specifications. Unused I/O pins are automatically tristated by the Designer software.

LP Low Power Pin

Controls the low power mode of the eX devices. The device is placed in the low power mode by connecting the LP pin to logic HIGH. In low power mode, all I/Os are tristated, all input buffers are turned OFF, and the core of the device is turned OFF. To exit the low power mode, the LP pin must be set LOW. The device enters the low power mode 800 ns after the LP pin is driven to a logic HIGH. It will resume normal operation 200 μ s after the LP pin is driven to a logic LOW. LP pin should not be left floating. Under normal operating condition it should be tied to GND via 10 k Ω resistor.

NC No Connection

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

PRA/PRB, I/O Probe A/B

The Probe pin is used to output data from any user-defined design node within the device. This diagnostic pin can be used independently or in conjunction with the other probe pin to allow real-time diagnostic output of any signal path within the device. The Probe pin can be used as a user-defined I/O when verification has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality.

TCK, I/O Test Clock

Test clock input for diagnostic probe and device programming. In flexible mode, TCK becomes active when the TMS pin is set LOW (refer to [Table 1-4 on page 1-10](#)). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state.

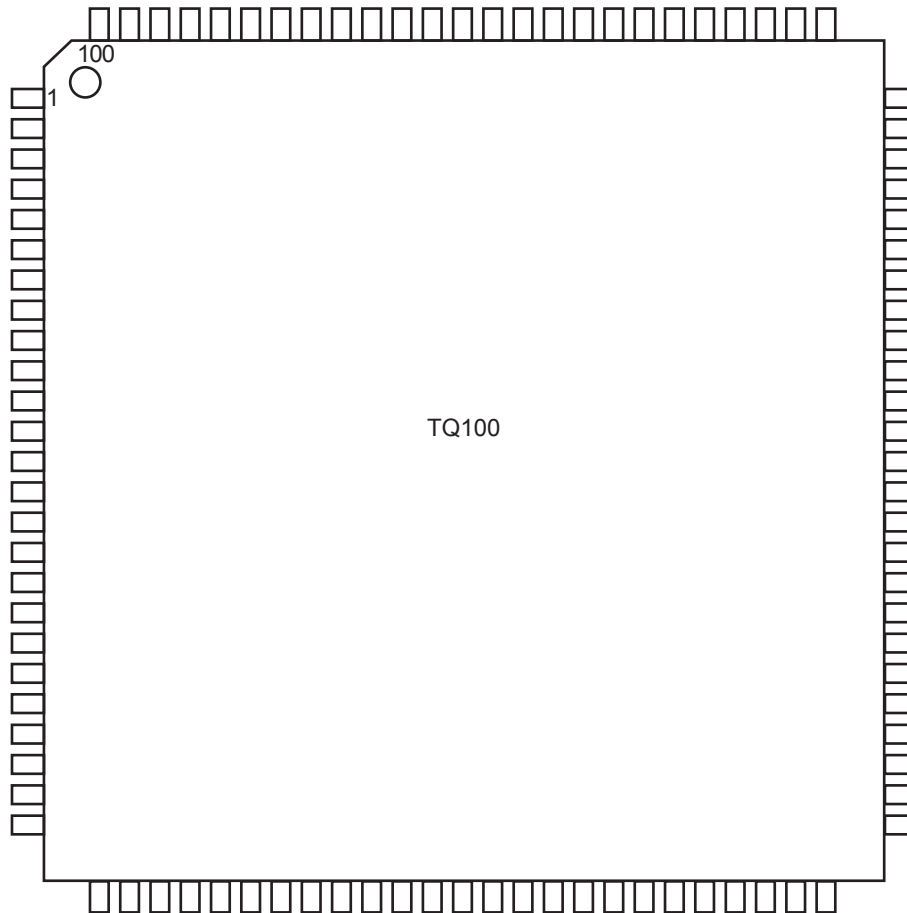
TDI, I/O Test Data Input

Serial input for boundary scan testing and diagnostic probe. In flexible mode, TDI is active when the TMS pin is set LOW (refer to [Table 1-4 on page 1-10](#)). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state.

TDO, I/O Test Data Output

Serial output for boundary scan testing. In flexible mode, TDO is active when the TMS pin is set LOW (refer to [Table 1-4 on page 1-10](#)). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state. When Silicon Explorer is being used, TDO will act as an output when the "checksum" command is run. It will return to user I/O when "checksum" is complete.

TQ100



Note: For Package Manufacturing and Environmental information, visit Resource center at www.microsemi.com/soc/products/rescenter/package/index.html.

3 – Datasheet Information

List of Changes

The following table lists critical changes that were made in the current version of the document.

Revision	Changes	Page
Revision 10 (October 2012)	The "User Security" section was revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement industry standard security (SAR 34677).	1-5
	Package names used in the "Product Profile" section and "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34779).	I 2-1
Revision 9 (June 2011)	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "eX Device Status" table indicates the status for each device in the device family.	II
	The Chip Scale packages (CS49, CS128, CS181) are no longer offered for eX devices. They have been removed from the product family information. Pin tables for CSP packages have been removed from the datasheet (SAR 32002).	N/A
Revision 8 (v4.3, June 2006)	The "Ordering Information" was updated with RoHS information. The TQFP measurement was also updated.	II
	The "Dedicated Test Mode" was updated.	1-10
	Note 5 was added to the "3.3 V LVTTTL Electrical Specifications" and "5.0 V TTL Electrical Specifications" tables	1-18
	The "LP Low Power Pin" description was updated.	1-31
Revision 7 (v4.2, June 2004)	The "eX Timing Model" was updated.	1-22
v4.1	The "Development Tool Support" section was updated.	1-13
	The "Package Thermal Characteristics" section was updated.	1-21
v4.0	The "Product Profile" section was updated.	1-I
	The "Ordering Information" section was updated.	1-II
	The "Temperature Grade Offerings" section is new.	1-III
	The "Speed Grade and Temperature Grade Matrix" section is new.	1-III
	The "eX FPGA Architecture and Characteristics" section was updated.	1-1
	The "Clock Resources" section was updated.	1-3
	Table 1-1 •Connections of Routed Clock Networks, CLKA and CLKB is new.	1-4
	The "User Security" section was updated.	1-5
	The "I/O Modules" section was updated.	1-5
	The "Hot-Swapping" section was updated.	1-6
	The "Power Requirements" section was updated.	1-6
	The "Low Power Mode" section was updated.	1-6
	The "Boundary Scan Testing (BST)" section was updated.	1-10
	The "Dedicated Test Mode" section was updated.	1-10

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the ["eX Device Status" table on page II](#), is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

Export Administration Regulations (EAR)

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